

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Kenichi MACHIDA

Application No.: New US Patent Application

Filed: February 28, 2002

Docket No.: 112069.01

For: PHOTOCHEMICAL HOLE BURNING MEDIA

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 3 and 12 as follows:

3. (Amended) The photochemical hole burning medium set forth in claim 1, wherein said rare earth complex and said reducing agent constitute an electron-donating composite compound.
12. (Amended) The photochemical hole burning medium set forth in claim 1, wherein said solid matrix is at least one glass-forming compound selected from the group consisting of silica, germanium oxide, boron oxide, phosphorous pentaoxide and tellurium oxide.

REMARKS

Claims 1-42 are pending. By this Preliminary Amendment, claims 3 and 12 are amended to eliminate multiple dependencies. Prompt and favorable consideration on the merits is respectfully requested.

The attached Appendix includes marked-up copies of each rewritten claim (37 C.F.R. §1.121(c)(1)(ii)).

Respectfully submitted,



James A. Oliff
Registration No. 27,075

Thomas J. Pardini
Registration No. 30,411

JAO:TJP/zmc

Attached: APPENDIX

Date: February 28, 2002

OLIFF & BERRIDGE, PLC
P.O. Box 19928
Alexandria, Virginia 22320
Telephone: (703) 836-6400

DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461
--

APPENDIX

Changes to Claims:

3. (Amended) The photochemical hole burning medium set forth in claim 1-~~or 2~~, wherein said rare earth complex and said reducing agent constitute an electron-donating composite compound.

12. (Amended) The photochemical hole burning medium set forth in claim 1-~~or 2~~, wherein said solid matrix is at least one glass-forming compound selected from the group consisting of silica, germanium oxide, boron oxide, phosphorous pentaoxide and tellurium oxide.